[DOCUMENT NAME] ABSTRACT OF DISCLOSURE

[ABSTRACT]

[TITLE OF THE INVENTION] SILICON WAFER AND METHOD FOR MANUFACTURING THE SAME

[PROBLEM]

To provide a silicon wafer which can suppress both slip dislocation and occurrence of warpage in a device manufacturing process and a method for manufacturing the same.

[SOLVING MEANS]

In a silicon wafer including plate-shaped BMDs, a density of BMDs whose diagonal lengths are in a range of 10nm to 120nm, of BMDs present at a deep position which is inwardly spaced from a surface of a silicon wafer by a distance of 50μm or more, is $1 \times 10^{11}/cm^3$ or more, a density of BMDs whose diagonal lengths are 750nm or more, of BMDs present at a deep position which is inwardly spaced from a surface of a silicon wafer by a distance of 50μm or more is $1 \times 10^{7}/cm^3$ or less, and an interstitial oxygen concentration is 5×10^{17}atoms/cm^3 or less.

FIG. 1